UNISONIC TECHNOLOGIES CO., LTD

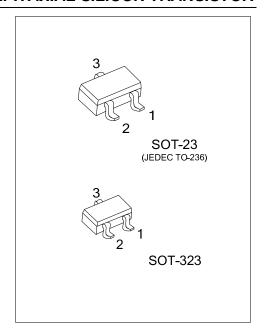
DTA115E

PNP EPITAXIAL SILICON TRANSISTOR

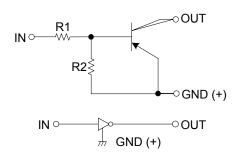
PNP DIGITAL TRANSISTOR (BUILT-IN RESISTORS)

■ FEATURES

- * Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors (see the equivalent circuit).
- * The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input They also have the advantage of almost completely eliminating parasitic effects.
- * Only the on / off conditions need to be set for operation, making device design easy.



EQUIVALENT CIRCUIT

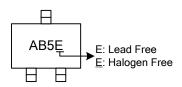


ORDERING INFORMATION

Ordering Number		Dookogo	Pin Assignment			Docking	
Lead Free	Halogen Free	Package	1	2	3	Packing	
DTA115EL-AE3-R	DTA115EG-AE3-R	SOT-23	G	I	0	Tape Reel	
DTA115EL-AL3-R	DTA115EG-AL3-R	SOT-323	G	ı	0	Tape Reel	

Note: Pin Assignment: G: GND I: IN O: OUT

MARKING



www.unisonic.com.tw 1 of 2 QW-R220-016,Ba

■ ABSOLUATE MAXIUM RATINGS (T_A= 25°C, unless otherwise specified.)

PARAMETER	PARAMETER SYMBOL RATINGS		UNIT
Supply Voltage	Vcc	-50	V
Input Voltage	V _{IN}	-40~+10	V
Outrat Comment	l _{оит}	-20	^
Output Current	I _{C(MAX)}	-100	mA
Power Dissipation	P _D	200	mW
Junction Temperature	TJ	150	$^{\circ}\mathbb{C}$
Storage Temperature	T _{STG}	-40 ~ +150	°C

Note Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (T_A= 25°C, unless otherwise specified.)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
Input Voltage	V _{IN(OFF)}	V _{CC} = -5V, I _{OUT} =-100μA			-0.5	V	
	V _{IN(ON)}	V_{OUT} = -0.3V, I_{OUT} = -1mA	-3			V	
Output Voltage	$V_{OUT(ON)}$	I _{OUT} = -5mA, I _{IN} = -0.25mA		-0.1	-0.3	V	
Input Current	I _{IN}	V _{IN} = -5V			-0.15	mA	
Output Current	I _{OUT(OFF)}	V _{CC} = -50V , V _{IN} =0V			-0.5	μΑ	
DC Current Gain	Gı	V_{OUT} = -5V, I_{OUT} = -5mA	82				
Input Resistance	R ₁		70	100	130	kΩ	
Resistance Ratio	R ₂ /R ₁		8.0	1	1.2		
Transition Frequency	f _T	V _{CE} = -10 V, I _E = 5mA, f=100MHz (Note)		250		MHz	

Note: Transition frequency of the device

UTC assumes no responsibility for equipment failures that result from using products at values that exceed, even momentarily, rated values (such as maximum ratings, operating condition ranges, or other parameters) listed in products specifications of any and all UTC products described or contained herein. UTC products are not designed for use in life support appliances, devices or systems where malfunction of these products can be reasonably expected to result in personal injury. Reproduction in whole or in part is prohibited without the prior written consent of the copyright owner. The information presented in this document does not form part of any quotation or contract, is believed to be accurate and reliable and may be changed without notice.

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for Bipolar Transistors - Pre-Biased category:

Click to view products by Unisonic manufacturer:

Other Similar products are found below:

MMUN2217LT1G FP101-TL-E RN1607(TE85L,F) DRC9A14E0L DTA124GKAT146 DTA144WETL DTA144WKAT146
DTC113EET1G DTC115TETL DTC115TKAT146 DTC124TETL DTC144ECA-TP DTC144VUAT106 MUN5241T1G

BCR158WH6327XTSA1 NSBA114TDP6T5G NSBA143TF3T5G NSBA143ZF3T5G NSBC114EF3T5G NSBC114YF3T5G

NSBC123TF3T5G NSBC143TF3T5G NSVMUN2212T1G NSVMUN5111DW1T3G NSVMUN5314DW1T3G NSVUMC2NT1G

SMMUN2134LT1G SMUN2212T1G SMUN5235T1G SMUN5330DW1T1G SSVMUN5312DW1T2G 2SC3650-TD-E RN1303(TE85L,F)

RN4605(TE85L,F) BCR135SH6327XT TTEPROTOTYPE79 UMC3NTR DTA113EET1G EMA2T2R EMH15T2R SDTA114YET1G

SMMUN2111LT3G SMMUN2113LT1G SMMUN2114LT1G SMMUN2211LT3G SMUN2214T3G SMUN5113DW1T1G

SMUN5335DW1T1G NSBA114YF3T5G NSBC114TF3T5G